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IRFP460C

500V N-Channel MOSFET

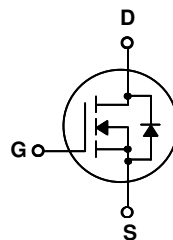
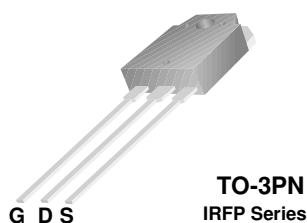
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies and power factor corrections.

Features

- 20A, 500V, $R_{DS(on)} = 0.24\Omega @ V_{GS} = 10V$
- Low gate charge (typical 130nC)
- Low C_{rss} (typical 60 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	IRFP460C	Units
V_{DSS}	Drain-Source Voltage	500	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	20	A
		12.5	A
I_{DM}	Drain Current - Pulsed (Note 1)	80	A
V_{GSS}	Gate-Source Voltage	± 30	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	1050	mJ
I_{AR}	Avalanche Current (Note 1)	20	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	23.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	235	W
		1.88	W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.53	$^\circ\text{C/W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.24	--	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	500	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.55	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 400\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 10.0\text{ A}$	--	0.2	0.24	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 10.0\text{ A}$ (Note 4)	--	18	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	4590	6000	pF
C_{oss}	Output Capacitance		--	380	460	pF
C_{rss}	Reverse Transfer Capacitance		--	60	80	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250\text{ V}, I_D = 20\text{ A},$ $R_G = 25\ \Omega$ (Note 4, 5)	--	50	120	ns
t_r	Turn-On Rise Time		--	150	310	ns
$t_{d(off)}$	Turn-Off Delay Time		--	380	770	ns
t_f	Turn-Off Fall Time		--	180	370	ns
Q_g	Total Gate Charge	$V_{DS} = 400\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	130	170	nC
Q_{gs}	Gate-Source Charge		--	20	--	nC
Q_{gd}	Gate-Drain Charge		--	45	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	20	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	80	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 20\text{ A}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 20\text{ A},$	--	480	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	7.7	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 5.1\text{ mH}, I_{AS} = 20\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 20\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

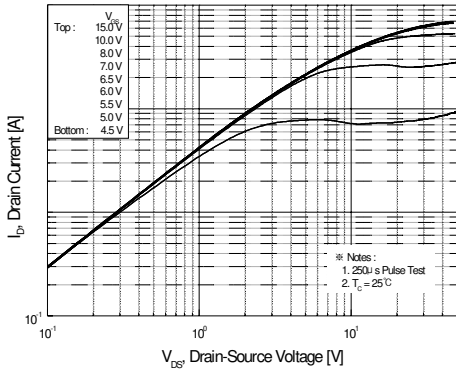


Figure 1. On-Region Characteristics

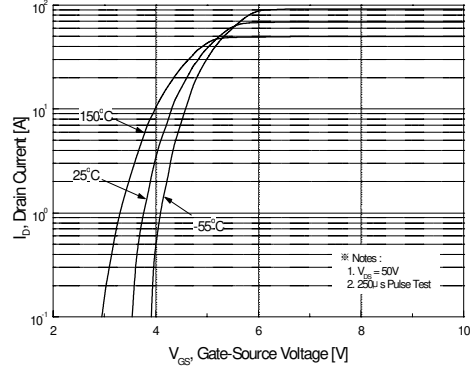


Figure 2. Transfer Characteristics

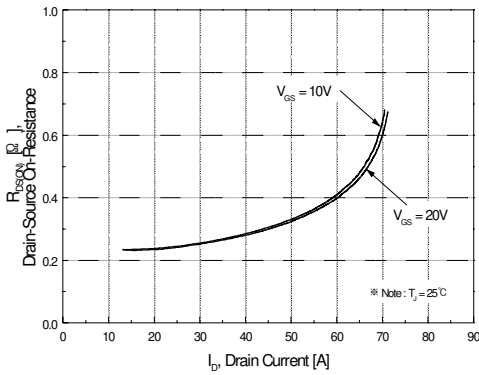


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

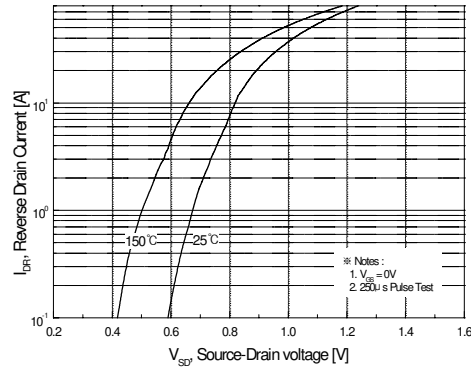


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

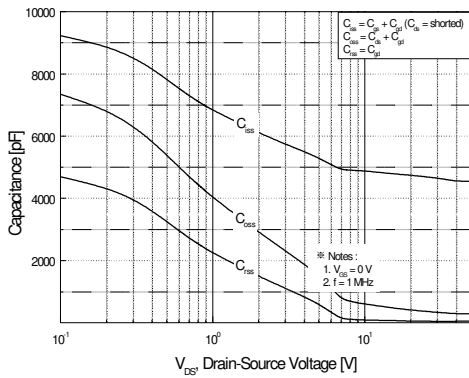


Figure 5. Capacitance Characteristics

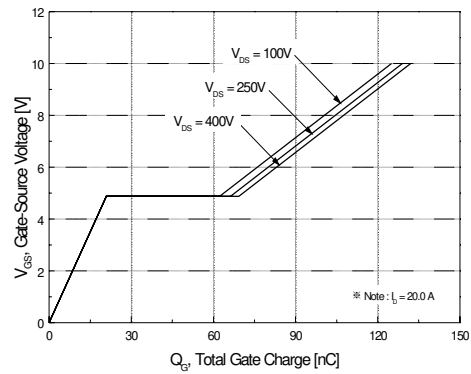


Figure 6. Gate Charge Characteristics

Dimensions in Millimeters

Typical Characteristics (Continued)

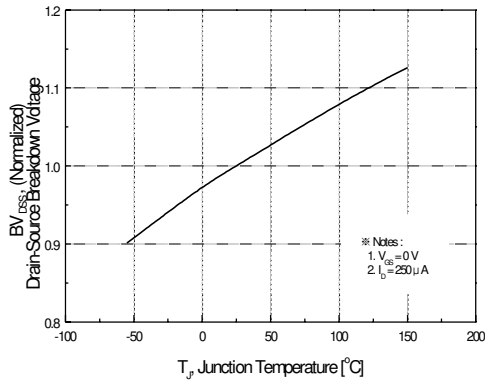


Figure 7. Breakdown Voltage Variation vs Temperature

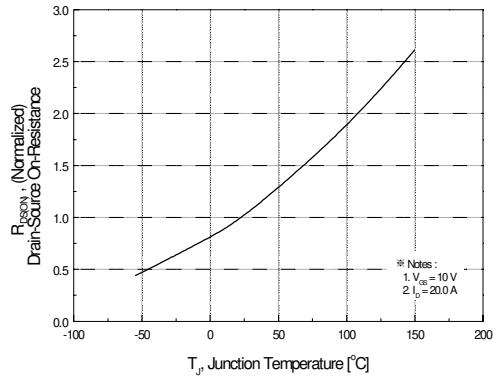


Figure 8. On-Resistance Variation vs Temperature

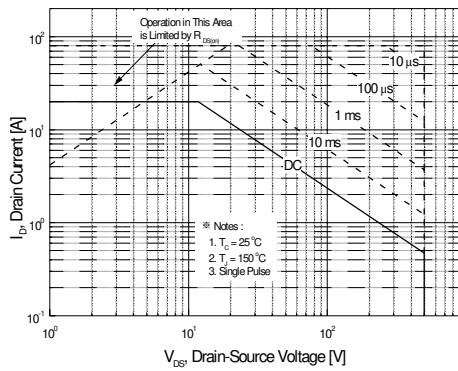


Figure 9. Maximum Safe Operating Area

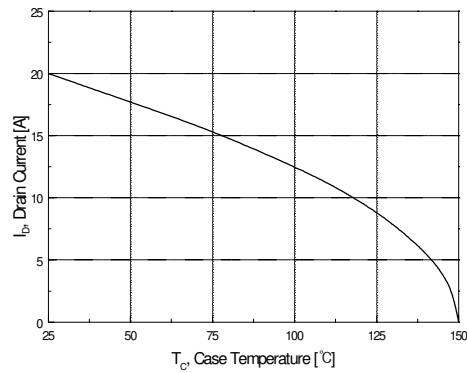


Figure 10. Maximum Drain Current vs Case Temperature

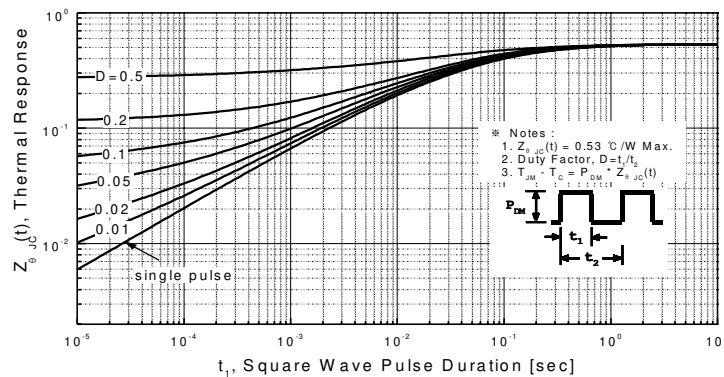
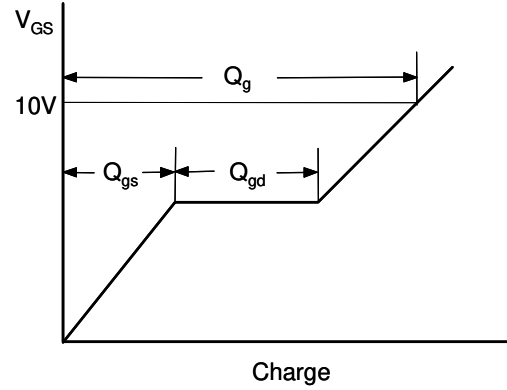
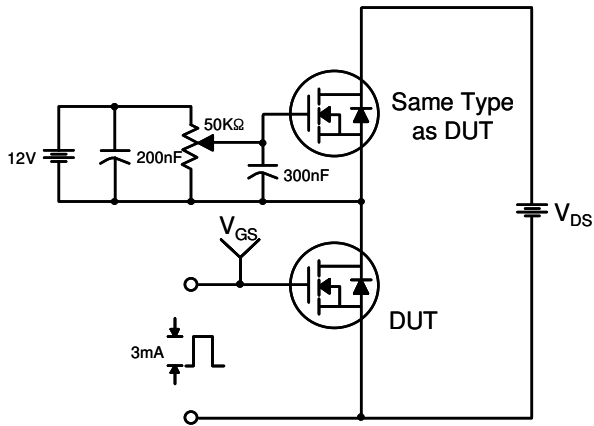


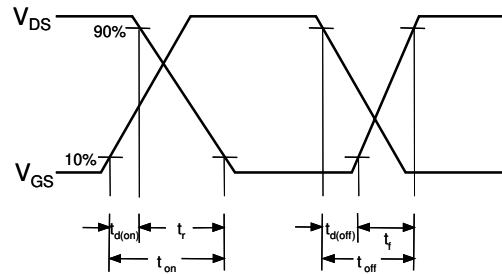
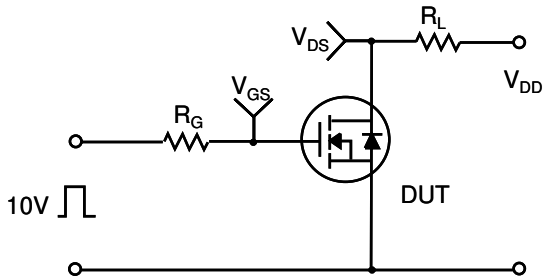
Figure 11. Transient Thermal Response Curve

Dimensions in Millimeters

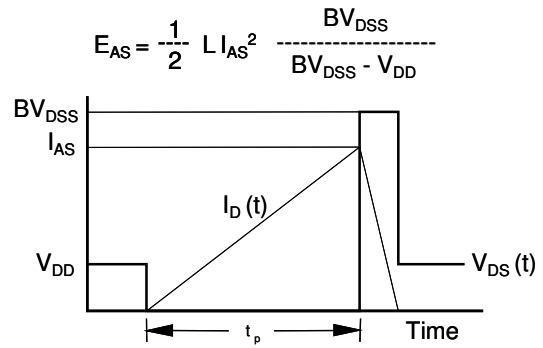
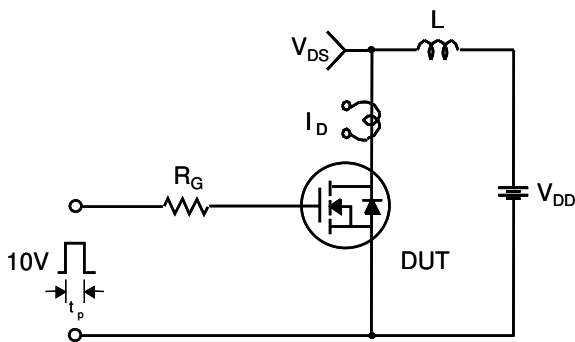
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

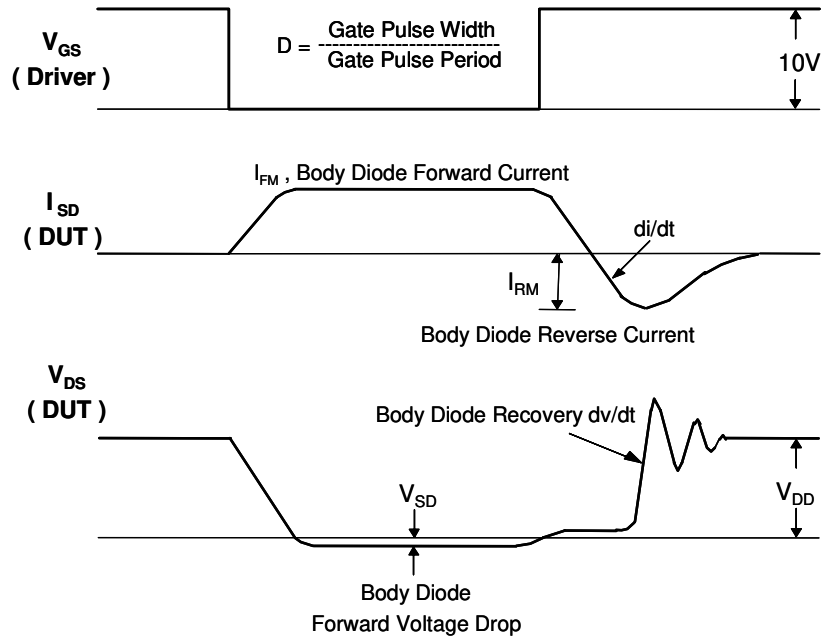
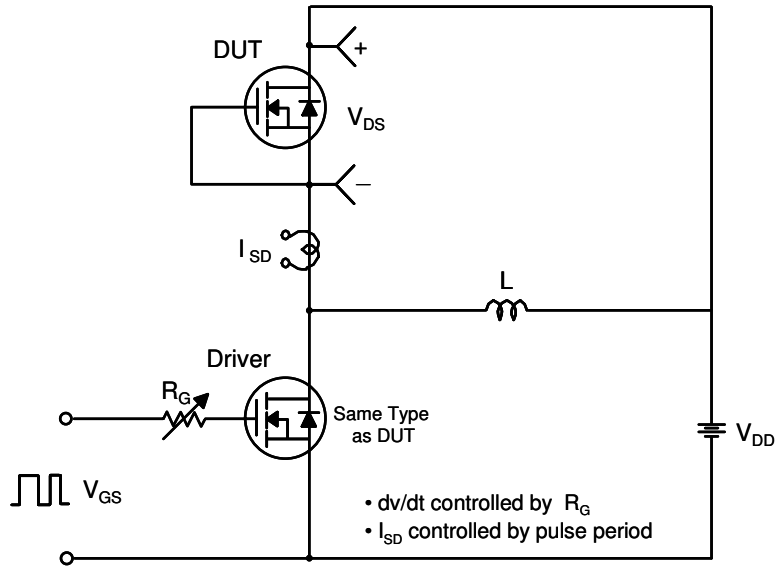


Unclamped Inductive Switching Test Circuit & Waveforms



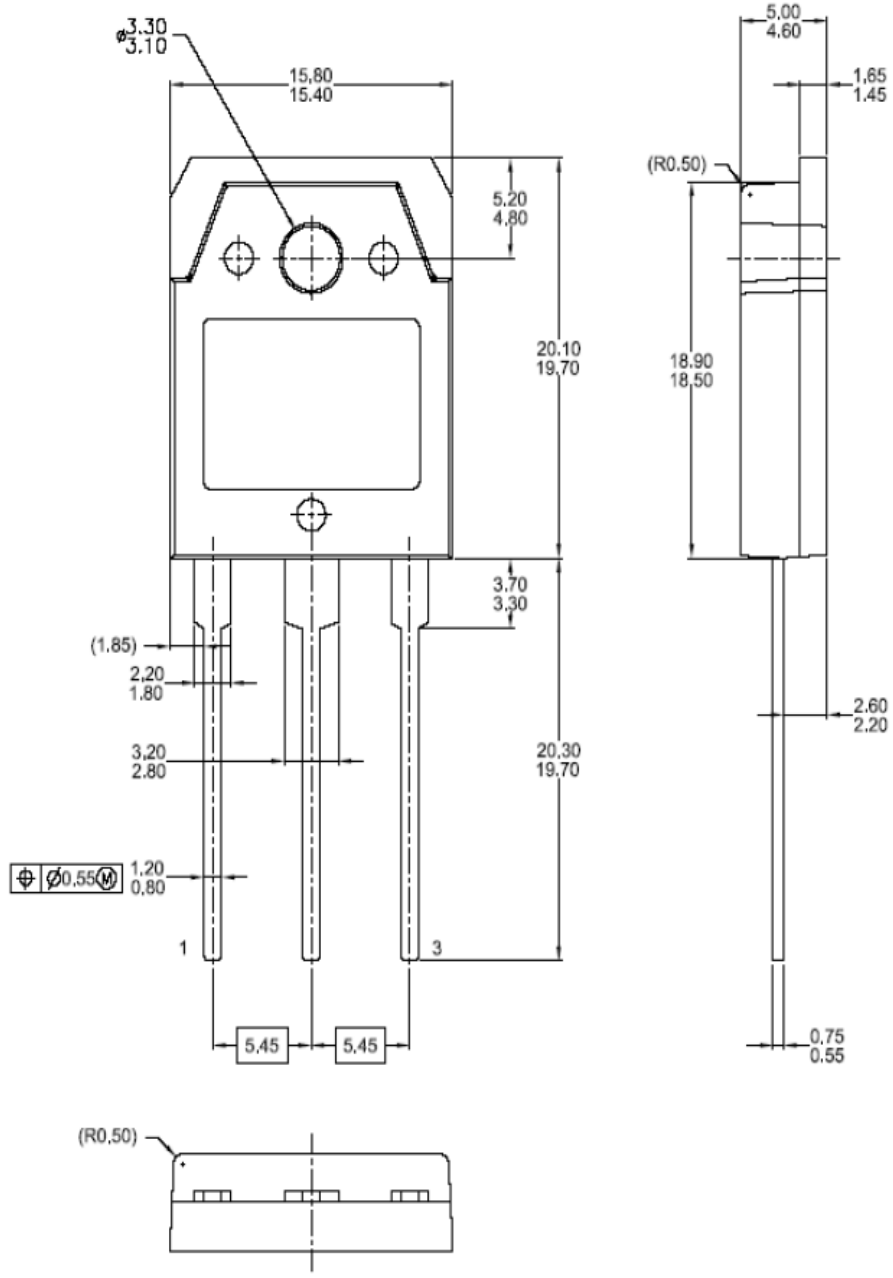
Dimensions in Millimeters

Peak Diode Recovery dv/dt Test Circuit & Waveforms



Mechanical Dimensions

TO-3PN



Dimensions in Millimeters

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